

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Lin, Shih-Yen; Tang, Shiang-Feng; Lee, Si-Chen; Kuan, Chieh-Hsiung
Assignee: National Science Council
Title: Quantum Dot Infrared Photodetector And Method For Fabricating The Same
Serial No.: Unknown Filing Date: Herewith
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PRELIMINARY AMENDMENT

Dear Sir:

Before examination on the merits, please amend the above application as follows:

IN THE CLAIMS

11. (Amended) The method according to claim 10, wherein said second undoped aluminum gallium arsenide layer has a thickness of about 50 nm.

In accordance with 37 CFR § 1.121(c)(1)(ii), Appendix A provides a marked up version of the claim containing the newly introduced change.


REMARKS

Claims 1-22 are pending. Claim 11 has been amended to correct a typographical error. Entry of this Preliminary Amendment is respectfully requested.

EXPRESS MAIL LABEL NO:

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Respectfully submitted,


Alan H. MacPherson
Attorney for Applicants
Reg. No. 24,423

LAW OFFICES OF
SKJERNEN MORRILL
MACPHERSON LLP

25 METRO DRIVE
SUITE 700
SAN JOSE, CA 95110
(408) 453-9200
FAX (408) 453-7979

APPENDIX A

In the following, insertions are underlined and deletions are enclosed in brackets.

11. (Amended) The method according to claim 10 [11], wherein said second undoped aluminum gallium arsenide layer has a thickness of about 50 nm.

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